

EUROPEAN PATENT OFFICE

Patent Abstracts of Japan

SC11482TP
BD

PUBLICATION NUMBER : 08130263
PUBLICATION DATE : 21-05-96

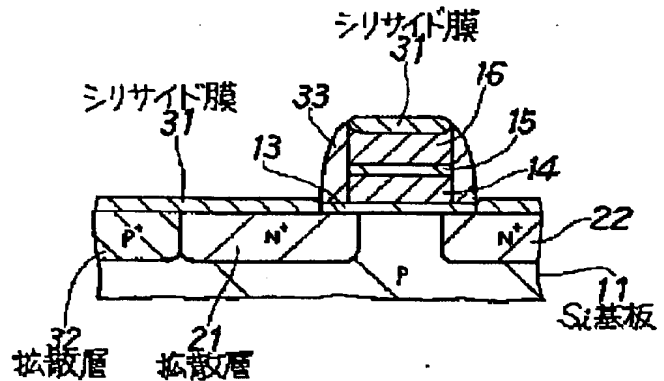
APPLICATION DATE : 28-10-94
APPLICATION NUMBER : 06288889

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INT.CL. : H01L 21/8247 H01L 29/788 H01L
29/792 H01L 27/115 H01L 29/78 H01L
21/336

TITLE : SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To realize fine patterning and high density while sustaining a diffusion layer, having conductivity type opposite to that of a semiconductor substrate, at same potential as the semiconductor substrate.

CONSTITUTION: N⁺ type and P⁺ type diffusion layers 21, 32 are provided on an Si substrate 11 and a silicide film 31 spreads while touching the surfaces of the diffusion layers 21, 32 thus equalizing the potential of the diffusion layer 21 and the Si substrate 11 through the diffusion layer 32 and the silicide film 31. Since no contact hole is required in the diffusion layers 21, 32 nor any wiring is required to be connected through a contact hole with the diffusion layers 21, 32, no region is required for the contact hole or the wiring.

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